

AMENDMENTS TO THE CLAIMS

Please replace the pending claims with the following claim listing:

1-49. **(Canceled)**

50. **(Currently Amended)** A nitride semiconductor structure comprising on a substrate:
an n-type collector layer;
a p-type base layer which is at least one of layers formed on said n-type collector layer; [[and]]

an n-type emitter layer formed on said p-type base layer, wherein layer;

an indium-containing p-type nitride semiconductor layer formed on a surface of said p-type base layer, which is exposed by etching said n-type emitter layer, is provided with an indium-containing p-type nitride semiconductor layer, which wherein said indium-containing p-type nitride semiconductor layer is regrown on said surface; and

a base electrode formed on said indium-containing p-type nitride semiconductor layer.

51. **(Original)** The nitride semiconductor structure according to claim 50, wherein said p-type nitride semiconductor layer is p-type InGaN.

52. **(Original)** The nitride semiconductor structure according to claim 51, wherein said p-type base layer is p-type InGaN.

53. **(Original)** The nitride semiconductor structure according to claim 51, wherein said p-type InGaN base layer has an indium mole fraction of 5 - 30%.

54. **(Original)** The nitride semiconductor structure according to claim 51, wherein said p-type nitride semiconductor layer has an indium mole fraction higher than an indium mole fraction of said p-type InGaN base layer.

55. **(Original)** The nitride semiconductor structure according to claim 50, wherein said p-type base layer is p-type InGaN.

56. **(Original)** The nitride semiconductor structure according to claim 55, wherein said p-type InGaN base layer has an indium mole fraction of 5 - 30%.

57. **(Original)** The nitride semiconductor structure according to claim 55, wherein said p-type nitride semiconductor layer has an indium mole fraction higher than an indium mole fraction of said p-type InGaN base layer.

58. **(Original)** The nitride semiconductor structure according to claim 50, wherein said p-type InGaN base layer has an indium mole fraction of 5 - 30%.

59. **(Original)** The nitride semiconductor structure according to claim 58, wherein said p-type nitride semiconductor layer has an indium mole fraction higher than an indium mole fraction of said p-type InGaN base layer.

60. **(Original)** The nitride semiconductor structure according to claim 50, wherein said p-type nitride semiconductor layer has an indium mole fraction higher than an indium mole fraction of said p-type InGaN base layer.

61.-76. **(Cancelled)**

77. **(Previously Presented)** The nitride semiconductor structure according to claim 50, further comprising a graded layer between said p-type base layer and said n-type collector layer, said graded layer has its indium mole fraction varied gradually.

78. **(Previously Presented)** The nitride semiconductor structure according to claim 51, further comprising a graded layer between said p-type base layer and said n-type collector layer, said graded layer has its indium mole fraction varied gradually.

79. **(Previously Presented)** The nitride semiconductor structure according to claim 55, further comprising a graded layer between said p-type base layer and said n-type collector layer, said graded layer has its indium mole fraction varied gradually.